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Understanding Embedded - FPGAs (Field Programmable Gate Array)

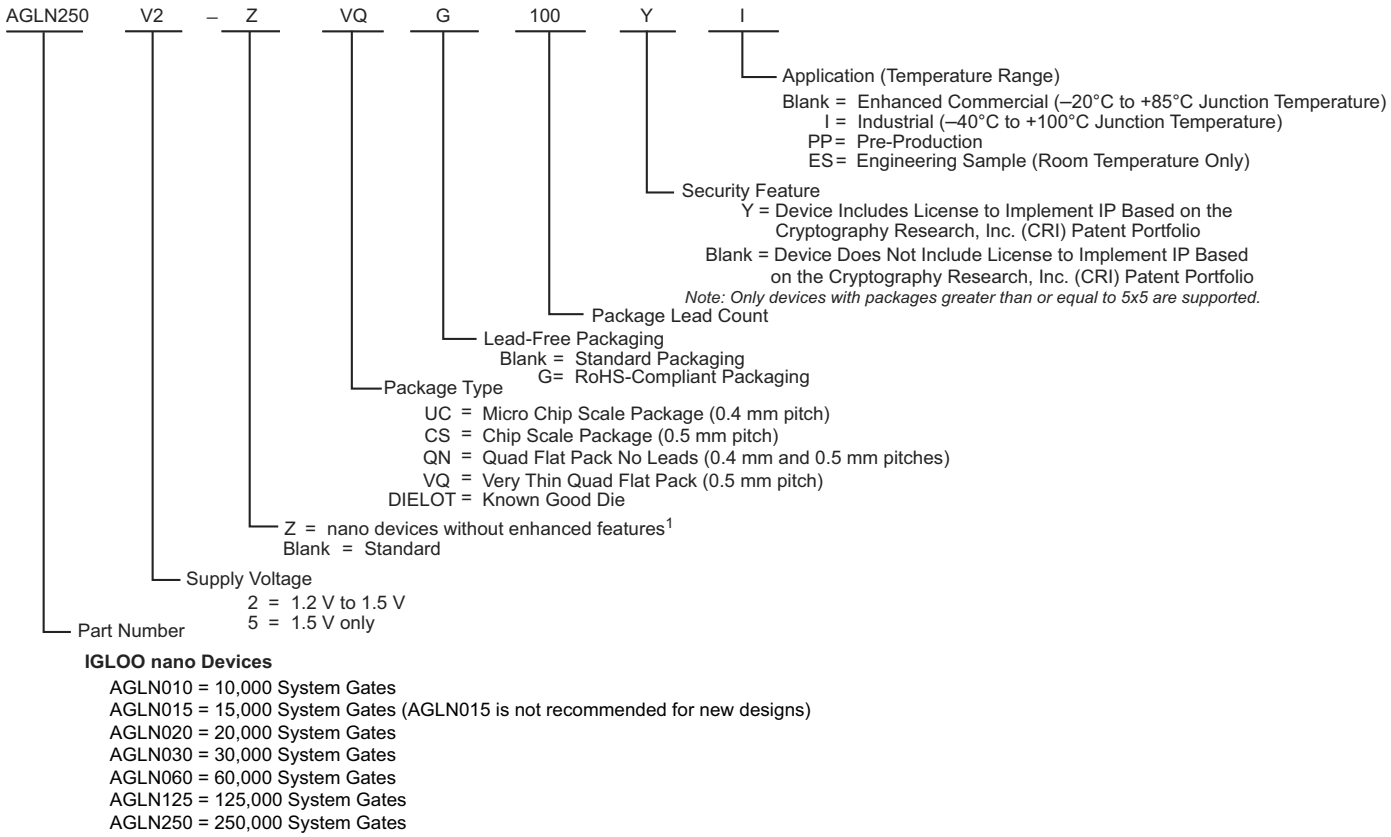
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	1536
Total RAM Bits	18432
Number of I/O	60
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	81-WFBGA, CSBGA
Supplier Device Package	81-CSP (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agln060v5-zcsg81

IGLOO nano Ordering Information



IGLOO nano Devices

AGLN010 = 10,000 System Gates
AGLN015 = 15,000 System Gates (AGLN015 is not recommended for new designs)
AGLN020 = 20,000 System Gates
AGLN030 = 30,000 System Gates
AGLN060 = 60,000 System Gates
AGLN125 = 125,000 System Gates
AGLN250 = 250,000 System Gates

Notes:

1. *Z-feature grade devices AGLN060Z, AGLN125Z, and AGLN250Z do not support the enhanced nano features of Schmitt Trigger input, bus hold (hold previous I/O state in Flash*Freeze mode), cold-sparing, hot-swap I/O capability and 1.2 V programming. The AGLN030 Z feature grade does not support Schmitt trigger input, bus hold and 1.2 V programming. For the VQ100, CS81, UC81, QN68, and QN48 packages, the Z feature grade and the N part number are not marked on the device. Z feature grade devices are not recommended for new designs.*
2. *AGLN030 is available in the Z feature grade only.*
3. *Marking Information: IGLOO nano V2 devices do not have a V2 marking, but IGLOO nano V5 devices are marked with a V5 designator.*

Devices Not Recommended For New Designs

AGLN015, AGLN030Z, AGLN060Z, AGLN125Z, and AGLN250Z are not recommended for new designs. For more information on obsoleted devices/packages, refer to the *PDN1503 - IGLOO nano Z and ProASIC3 nano Z Families*.

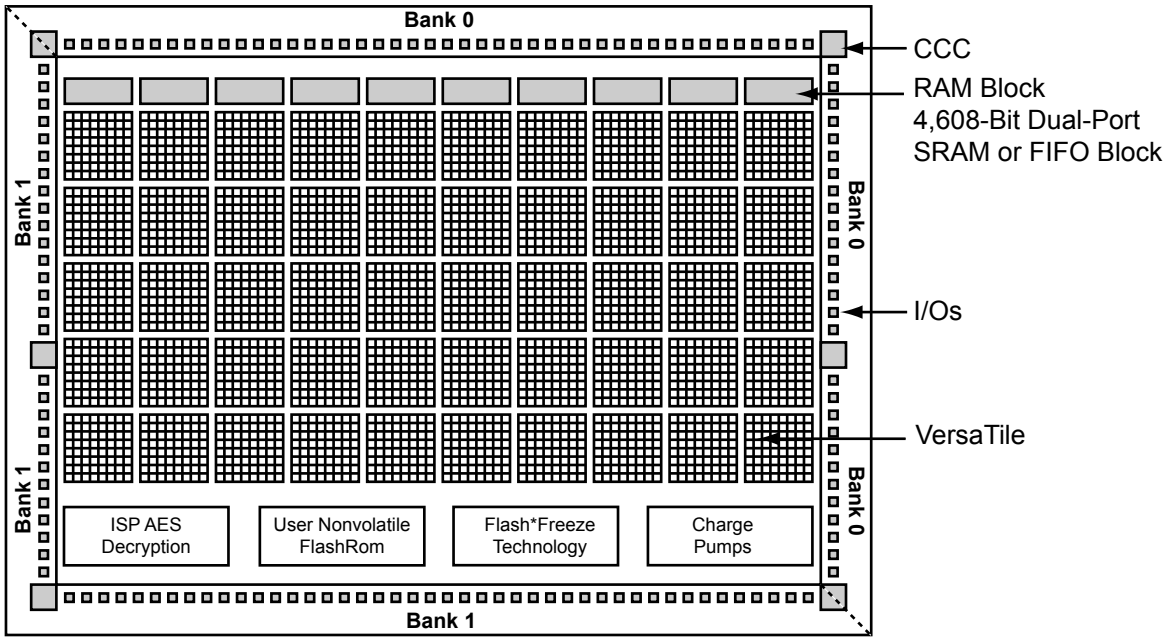


Figure 1-3 • **IGLOO Device Architecture Overview with Two I/O Banks (AGLN060, AGLN125)**

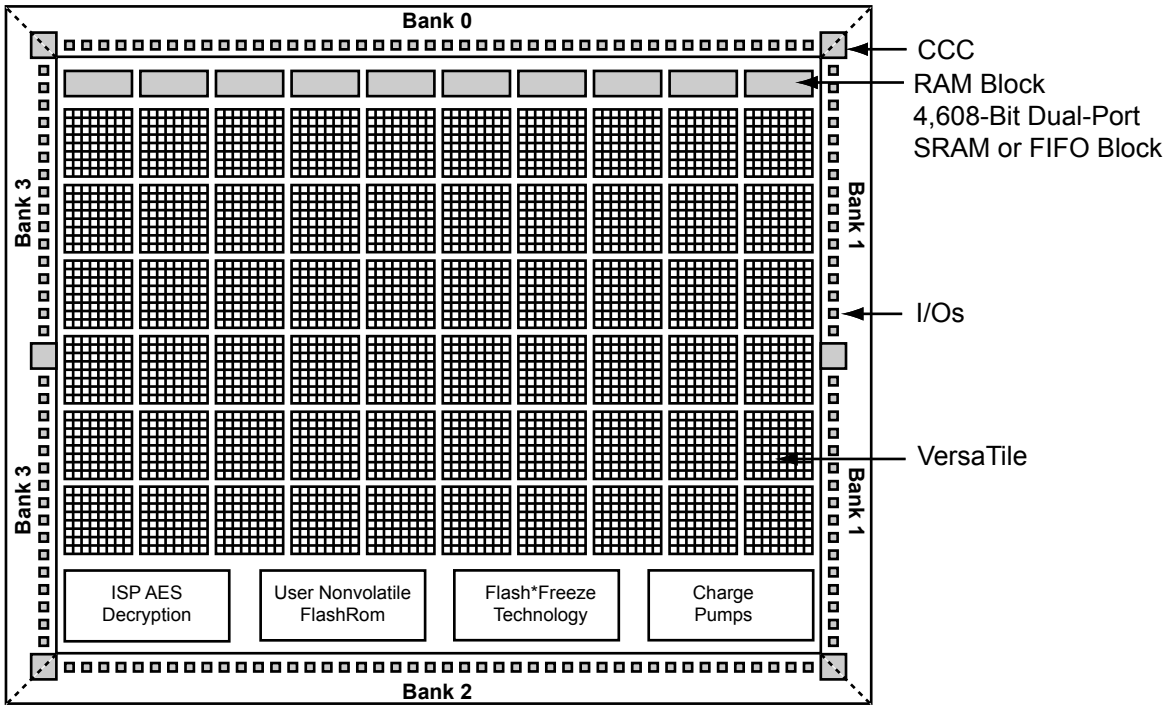


Figure 1-4 • **IGLOO Device Architecture Overview with Four I/O Banks (AGLN250)**

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User's Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-7 on page 1-9).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

   1 – I/O is set to drive out logic High

   0 – I/O is set to drive out logic Low

   Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

   Z -Tri-State: I/O is tristated

Figure 1-7 • **I/O States During Programming Window**

Thermal Characteristics

Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction temperature to be higher than the ambient temperature.

EQ 1 can be used to calculate junction temperature.

T_J = Junction Temperature = $\Delta T + T_A$

EQ 1

where:

T_A = Ambient temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Figure 2-5.

P = Power dissipation

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja}. The thermal characteristics for θ_{ja} are shown for two air flow rates. The maximum operating junction temperature is 100°C. EQ 2 shows a sample calculation of the maximum operating power dissipation allowed for a 484-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. } (°C) - \text{Max. ambient temp. } (°C)}{\theta_{ja}(°C/W)} = \frac{100°C - 70°C}{20.5°C/W} = 1.46 \text{ W}$$

EQ 2

Table 2-5 • **Package Thermal Resistivities**

Package Type	Pin Count	θ_{jc}	θ_{ja}			Units
			Still Air	200 ft./ min.	500 ft./ min.	
Chip Scale Package (CSP)	36	TBD	TBD	TBD	TBD	C/W
	81	TBD	TBD	TBD	TBD	C/W
Quad Flat No Lead (QFN)	48	TBD	TBD	TBD	TBD	C/W
	68	TBD	TBD	TBD	TBD	C/W
	100	TBD	TBD	TBD	TBD	C/W
Very Thin Quad Flat Pack (VQFP)	100	10.0	35.3	29.4	27.1	C/W

Temperature and Voltage Derating Factors

Table 2-6 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 70°C, VCC = 1.425 V)**
For IGLOO nano V2 or V5 Devices, 1.5 V DC Core Supply Voltage

Array Voltage VCC (V)	Junction Temperature (°C)						
	–40°C	–20°C	0°C	25°C	70°C	85°C	100°C
1.425	0.947	0.956	0.965	0.978	1.000	1.009	1.013
1.5	0.875	0.883	0.892	0.904	0.925	0.932	0.937
1.575	0.821	0.829	0.837	0.848	0.868	0.875	0.879

Table 2-10 • **Quiescent Supply Current (IDD) Characteristics, IGLOO nano Sleep Mode***

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
VCCI= 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	µA

Note: $*I_{DD} = N_{BANKS} * I_{CCI}$.

Table 2-11 • **Quiescent Supply Current (IDD) Characteristics, IGLOO nano Shutdown Mode**

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	0	0	0	0	µA

Table 2-12 • **Quiescent Supply Current (IDD), No IGLOO nano Flash*Freeze Mode[1]**

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
ICCA Current[2]								
Typical (25°C)	1.2 V	3.7	5	5	10	13	18	µA
	1.5 V	8	14	14	20	28	44	µA
ICCI or IJTAG Current								
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI / VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI / VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI / VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI / VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	µA

Notes:

1. *$IDD = N_{BANKS} * ICCI + ICCA$. JTAG counts as one bank when powered.*
2. *Includes VCC, VCCPLL, and VPUMP currents.*

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength[2]	Slew Rate	VIL		VIH		VOL	VOH	IOL[1]	IOH[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range[3]	100 µA	8 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100 µA	100 µA
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS[4]	1 mA	1 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range[4,5]	100 µA	1 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	100 µA	100 µA

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.*
4. *Applicable to IGLOO nano V2 devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range, as specified in the JESD8-12 specification.*

Table 2-22 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions

	Commercial[1]		Industrial[2]	
	IIL [3]	IIH [4]	IIL [3]	IIH [4]
DC I/O Standards	µA	µA	µA	µA
3.3 V LVTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCOMS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
1.2 V LVCMOS[5]	10	10	15	15
1.2 V LVCMOS Wide Range[5]	10	10	15	15

Notes:

1. *Commercial range (–20°C < T_A < 70°C)*
2. *Industrial range (–40°C < T_A < 85°C)*
3. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions, where VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
4. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions, where –0.3 V < VIN < VIL.*
5. *Applicable to IGLOO nano V2 devices operating at VCCI ≥ VCC.*

The length of time an I/O can withstand IOSH/IOSL events depends on the junction temperature. The reliability data below is based on a 3.3 V, 8 mA I/O setting, which is the worst case for this type of analysis.

For example, at 100°C, the short current condition would have to be sustained for more than six months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

Table 2-31 • **Duration of Short Circuit Event before Failure**

Temperature	Time before Failure
–40°C	> 20 years
–20°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months

Table 2-32 • **Schmitt Trigger Input Hysteresis**
Hysteresis Voltage Value (Typ.) for Schmitt Mode Input Buffers

Input Buffer Configuration	Hysteresis Value (typ.)
3.3 V LVTTL / LVCMOS (Schmitt trigger mode)	240 mV
2.5 V LVCMOS (Schmitt trigger mode)	140 mV
1.8 V LVCMOS (Schmitt trigger mode)	80 mV
1.5 V LVCMOS (Schmitt trigger mode)	60 mV
1.2 V LVCMOS (Schmitt trigger mode)	40 mV

Table 2-33 • **I/O Input Rise Time, Fall Time, and Related I/O Reliability**

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTL/LVCMOS (Schmitt trigger disabled)	No requirement	10 ns *	20 years (100°C)
LVTTL/LVCMOS (Schmitt trigger enabled)	No requirement	No requirement, but input noise voltage cannot exceed Schmitt hysteresis.	20 years (100°C)

*Note: *The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, then the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi recommends signal integrity evaluation/characterization of the system to ensure that there is no excessive noise coupling into input signals.*

Applies to 1.2 V DC Core Voltage

Table 2-38 • **3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	1.55	4.09	0.26	0.97	1.36	1.10	4.16	3.91	2.19	2.64	ns
4 mA	STD	1.55	4.09	0.26	0.97	1.36	1.10	4.16	3.91	2.19	2.64	ns
6 mA	STD	1.55	3.45	0.26	0.97	1.36	1.10	3.51	3.32	2.43	3.03	ns
8 mA	STD	1.55	3.45	0.26	0.97	1.36	1.10	3.51	3.32	2.43	3.03	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-39 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	1.55	2.68	0.26	0.97	1.36	1.10	2.72	2.26	2.19	2.74	ns
4 mA	STD	1.55	2.68	0.26	0.97	1.36	1.10	2.72	2.26	2.19	2.74	ns
6 mA	STD	1.55	2.31	0.26	0.97	1.36	1.10	2.34	1.90	2.43	3.14	ns
8 mA	STD	1.55	2.31	0.26	0.97	1.36	1.10	2.34	1.90	2.43	3.14	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Fully Registered I/O Buffers with Asynchronous Clear

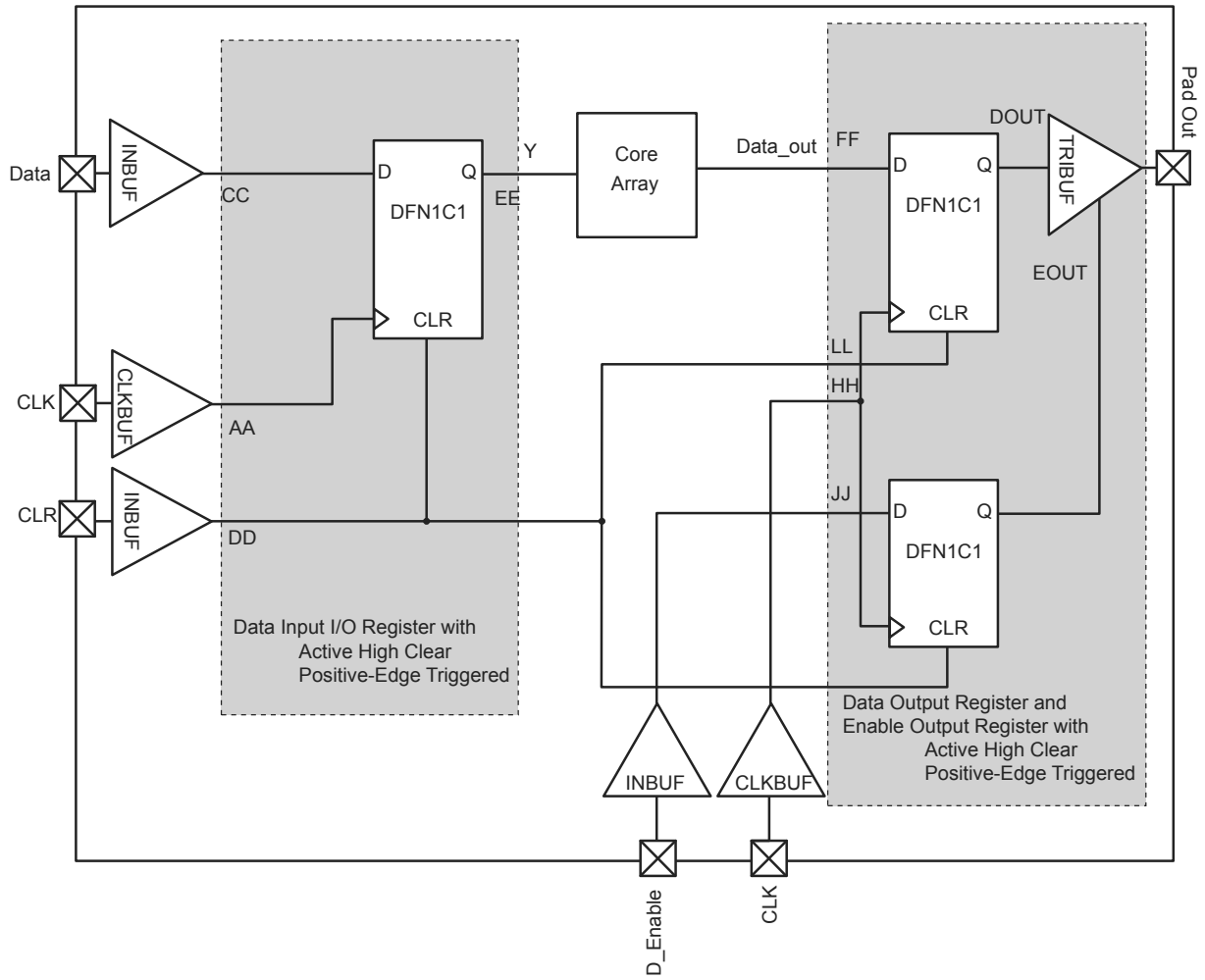


Figure 2-13 • **Timing Model of the Registered I/O Buffers with Asynchronous Clear**

Input Register

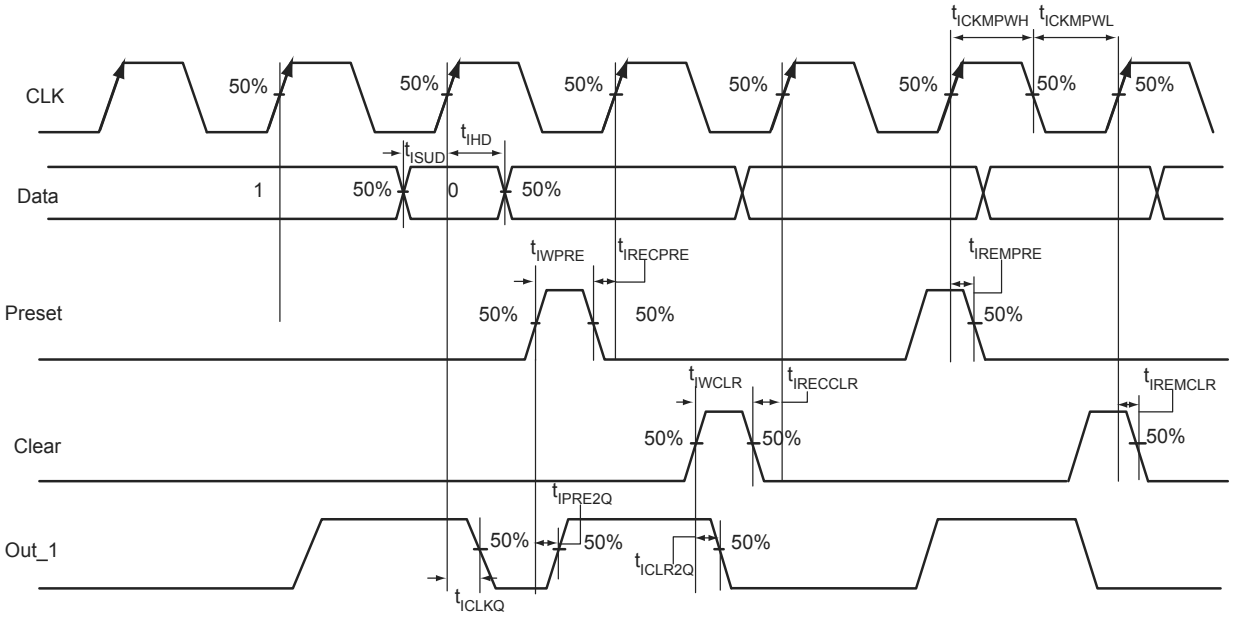


Figure 2-14 • **Input Register Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-72 • **Input Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.42	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.47	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.79	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.79	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width HIGH for the Input Data Register	0.31	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width LOW for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

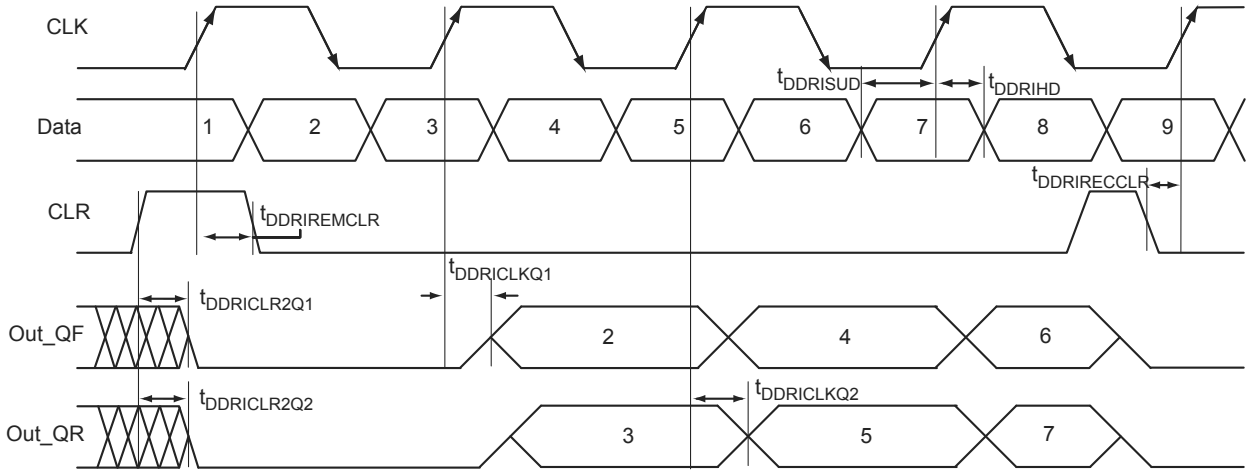


Figure 2-18 • **Input DDR Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-79 • **Input DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.25 V

Parameter	Description	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.48	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.65	ns
$t_{DDRISUD1}$	Data Setup for Input DDR (negedge)	0.50	ns
$t_{DDRISUD2}$	Data Setup for Input DDR (posedge)	0.40	ns
$t_{DDRIHD1}$	Data Hold for Input DDR (negedge)	0.00	ns
$t_{DDRIHD2}$	Data Hold for Input DDR (posedge)	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.82	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.98	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.23	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width HIGH for Input DDR	0.31	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width LOW for Input DDR	0.28	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-87 • Register Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	1.61	ns
t_{SUD}	Data Setup Time for the Core Register	1.17	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	1.29	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.87	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.89	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.24	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.46	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.46	ns
t_{CKMPWH}	Clock Minimum Pulse Width HIGH for the Core Register	0.95	ns
t_{CKMPWL}	Clock Minimum Pulse Width LOW for the Core Register	0.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Global Resource Characteristics

AGLN125 Clock Tree Topology

Clock delays are device-specific. Figure 2-25 is an example of a global tree used for clock routing. The global tree presented in Figure 2-25 is driven by a CCC located on the west side of the AGLN125 device. It is used to drive all D-flip-flops in the device.

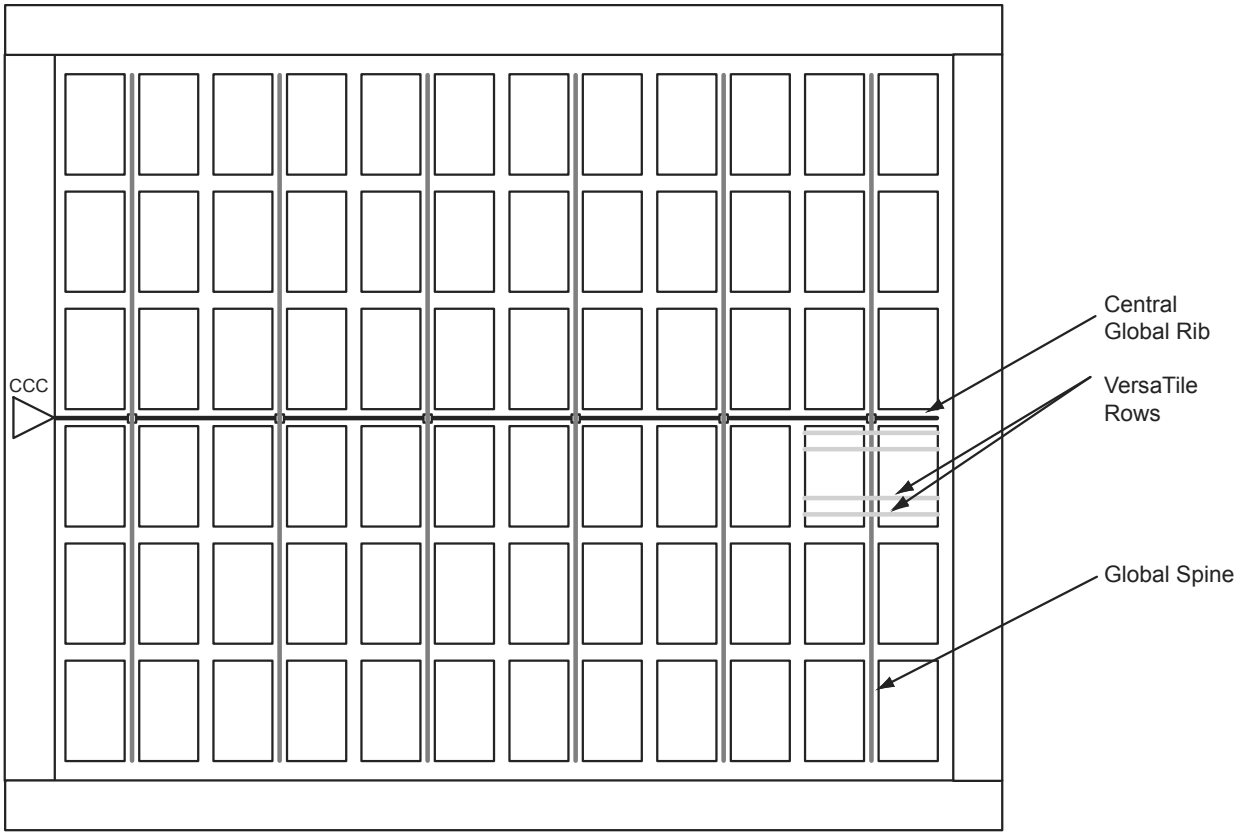


Figure 2-25 • **Example of Global Tree Use in an AGLN125 Device for Clock Routing**

***Table 2-105* • RAM512X18**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.28	ns
t_{AH}	Address hold time	0.25	ns
t_{ENS}	REN, WEN setup time	1.13	ns
t_{ENH}	REN, WEN hold time	0.13	ns
t_{DS}	Input data (WD) setup time	1.10	ns
t_{DH}	Input data (WD) hold time	0.55	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	6.56	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	2.67	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address; applicable to opening edge	0.87	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address; applicable to opening edge	1.04	ns
t_{RSTBQ}	RESET LOW to data out LOW on RD (flow through)	3.21	ns
	RESET LOW to data out LOW on RD (pipelined)	3.21	ns
$t_{REMRSTB}$	RESET removal	0.93	ns
$t_{RECRSTB}$	RESET recovery	4.94	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note AC374: Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based FPGAs and SoC FPGAs App Note.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

Table 3-1 shows the Flash*Freeze pin location on the available packages for IGLOO nano devices. The Flash*Freeze pin location is independent of device (except for a PQ208 package), allowing migration to larger or smaller IGLOO nano devices while maintaining the same pin location on the board. Refer to the "Flash*Freeze Technology and Low Power Modes" chapter of the *IGLOO nano FPGA Fabric User's Guide* for more information on I/O states during Flash*Freeze mode.

***Table 3-1* • Flash*Freeze Pin Locations for IGLOO nano Devices**

Package	Flash*Freeze Pin
CS81/UC81	H2
QN48	14
QN68	18
VQ100	27
UC36	E2

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements. Refer to Table 3-2 for more information.

***Table 3-2* • Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance [1,2]
VJTAG at 3.3 V	200 Ω to 1 kΩ
VJTAG at 2.5 V	200 Ω to 1 kΩ
VJTAG at 1.8 V	500 Ω to 1 kΩ
VJTAG at 1.5 V	500 Ω to 1 kΩ

Notes:

1. *The TCK pin can be pulled-up or pulled-down.*
2. *The TRST pin is pulled-down.*
3. *Equivalent parallel resistance if more than one device is on the JTAG chain*

CS81	
Pin Number	**AGLN060 Function**
A1	GAA0/IO02RSB0
A2	GAA1/IO03RSB0
A3	GAC0/IO06RSB0
A4	IO09RSB0
A5	IO13RSB0
A6	IO18RSB0
A7	GBB0/IO21RSB0
A8	GBA1/IO24RSB0
A9	GBA2/IO25RSB0
B1	GAA2/IO95RSB1
B2	GAB0/IO04RSB0
B3	GAC1/IO07RSB0
B4	IO08RSB0
B5	IO15RSB0
B6	GBC0/IO19RSB0
B7	GBB1/IO22RSB0
B8	IO26RSB0
B9	GBB2/IO27RSB0
C1	GAB2/IO93RSB1
C2	IO94RSB1
C3	GND
C4	IO10RSB0
C5	IO17RSB0
C6	GND
C7	GBA0/IO23RSB0
C8	GBC2/IO29RSB0
C9	IO31RSB0
D1	GAC2/IO91RSB1
D2	IO92RSB1
D3	GFA2/IO80RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	GCC2/IO43RSB0

CS81	
Pin Number	**AGLN060 Function**
D8	GCC1/IO35RSB0
D9	GCC0/IO36RSB0
E1	GFB0/IO83RSB1
E2	GFB1/IO84RSB1
E3	GFA1/IO81RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GCA1/IO39RSB0
E8	GCA0/IO40RSB0
E9	GCB2/IO42RSB0
F1[1]	VCCPLF
F2[1]	VCOMPLF
F3	GND
F4	GND
F5	VCCIB1
F6	GND
F7	GDA1/IO49RSB0
F8	GDC1/IO45RSB0
F9	GDC0/IO46RSB0
G1	GEA0/IO69RSB1
G2	GEC1/IO74RSB1
G3	GEB1/IO72RSB1
G4	IO63RSB1
G5	IO60RSB1
G6	IO54RSB1
G7	GDB2/IO52RSB1
G8	VJTAG
G9	TRST
H1	GEA1/IO70RSB1
H2	FF/GEB2/IO67RSB1
H3	IO65RSB1
H4	IO62RSB1
H5	IO59RSB1

CS81	
Pin Number	**AGLN060 Function**
H6	IO56RSB1
H7[2]	GDA2/IO51RSB1
H8	TDI
H9	TDO
J1	GEA2/IO68RSB1
J2	GEC2/IO66RSB1
J3	IO64RSB1
J4	IO61RSB1
J5	IO58RSB1
J6	IO55RSB1
J7	TCK
J8	TMS
J9	VPUMP

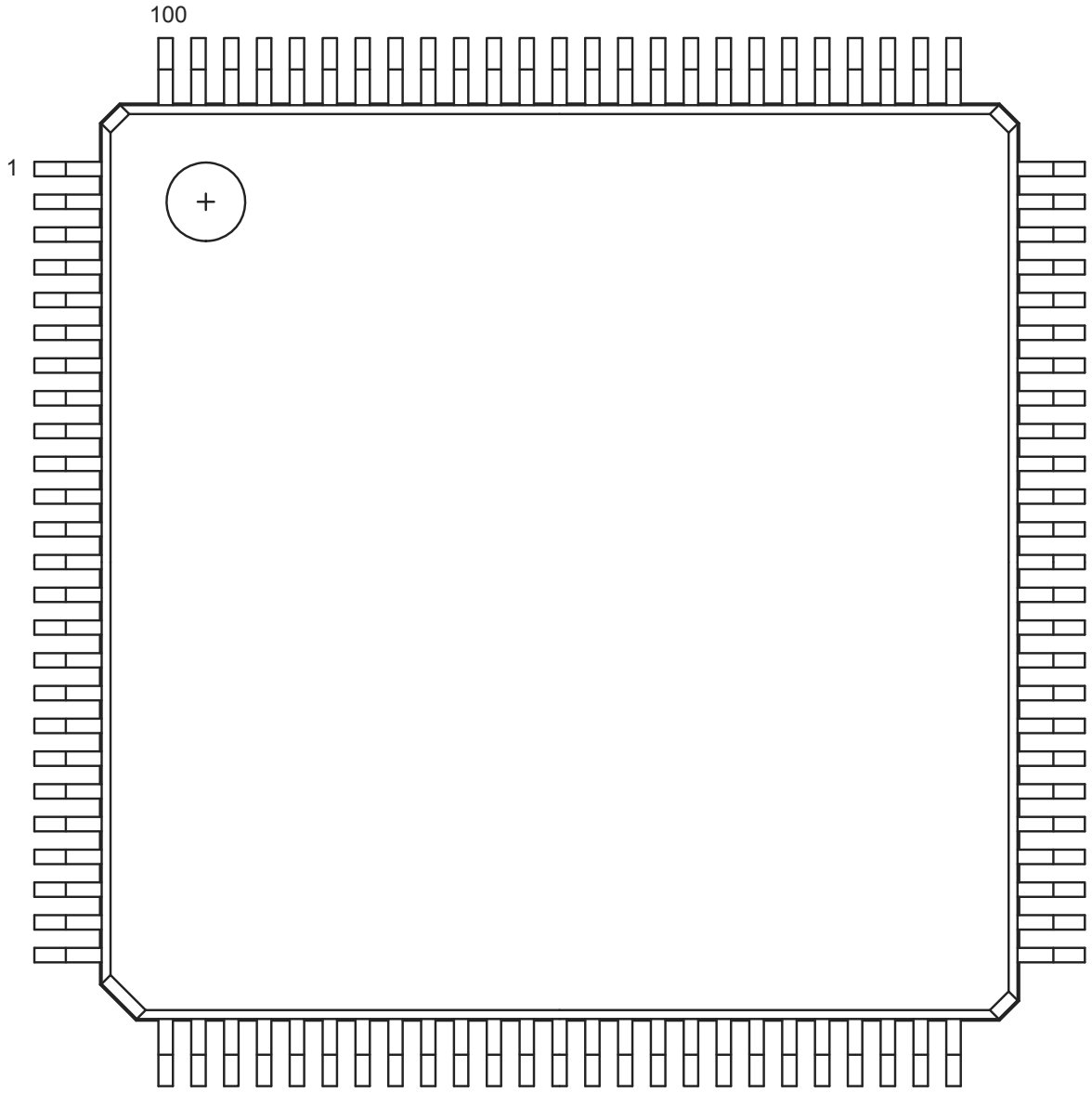
Notes:

1. *Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN060-CS81.*
2. *The bus hold attribute (hold previous I/O state in Flash*Freeze mode) is not supported for pin H7 in AGLN060-CS81.*

QN68	
Pin Number	**AGLN020 Function**
1	IO60RSB2
2	IO54RSB2
3	IO52RSB2
4	IO50RSB2
5	IO49RSB2
6	GEC0/IO48RSB2
7	GEA0/IO47RSB2
8	VCC
9	GND
10	VCCIB2
11	IO46RSB2
12	IO45RSB2
13	IO44RSB2
14	IO43RSB2
15	IO42RSB2
16	IO41RSB2
17	IO40RSB2
18	FF/IO39RSB1
19	IO37RSB1
20	IO35RSB1
21	IO33RSB1
22	IO31RSB1
23	IO30RSB1
24	VCC
25	GND
26	VCCIB1
27	IO27RSB1
28	IO25RSB1
29	IO23RSB1
30	IO21RSB1
31	IO19RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP

QN68	
Pin Number	**AGLN020 Function**
36	TDO
37	TRST
38	VJTAG
39	IO17RSB0
40	IO16RSB0
41	GDA0/IO15RSB0
42	GDC0/IO14RSB0
43	IO13RSB0
44	VCCIB0
45	GND
46	VCC
47	IO12RSB0
48	IO11RSB0
49	IO09RSB0
50	IO05RSB0
51	IO00RSB0
52	IO07RSB0
53	IO03RSB0
54	IO18RSB1
55	IO20RSB1
56	IO22RSB1
57	IO24RSB1
58	IO28RSB1
59	NC
60	GND
61	NC
62	IO32RSB1
63	IO34RSB1
64	IO36RSB1
65	IO61RSB2
66	IO58RSB2
67	IO56RSB2
68	IO63RSB2

VQ100



Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

Revision	Changes	Page
Revision 11 (Jul 2010)	The status of the AGLN060 device has changed from Advance to Production.	III
	The values for PAC1, PAC2, PAC3, and PAC4 were updated in Table 2-15 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices for 1.5 V core supply voltage (SAR 26404).	2-10
	The values for PAC1, PAC2, PAC3, and PAC4 were updated in Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices for 1.2 V core supply voltage (SAR 26404).	2-11
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "IGLOO nano Device Status" table on page III indicates the status for each device in the device family.	N/A
Revision 10 (Apr 2010)	References to differential inputs were removed from the datasheet, since IGLOO nano devices do not support differential inputs (SAR 21449).	N/A
	A parenthetical note, "hold previous I/O state in Flash*Freeze mode," was added to each occurrence of bus hold in the datasheet (SAR 24079).	N/A
	The "In-System Programming (ISP) and Security" section was revised to add 1.2 V programming.	I
	The note connected with the "IGLOO nano Ordering Information" table was revised to clarify features not available for Z feature grade devices.	IV
	The "IGLOO nano Device Status" table is new.	III
	The definition of C in the "Temperature Grade Offerings" table was changed to "extended commercial temperature range".	VI
	1.2 V wide range was added to the list of voltage ranges in the "I/Os with Advanced I/O Standards" section.	1-8
	A note was added to Table 2-2 • Recommended Operating Conditions [1] regarding switching from 1.2 V to 1.5 V core voltage for in-system programming. The VJTAG voltage was changed from "1.425 to 3.6" to "1.4 to 3.6" (SAR 24052). The note regarding voltage for programming V2 and V5 devices was revised (SAR 25213). The maximum value for VPUMP programming voltage (operation mode) was changed from 3.45 V to 3.6 V (SAR 25220).	2-2
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.14 V) were updated. Table 2-8 • Power Supply State per Mode is new.	2-6, 2-7
	The tables in the "Quiescent Supply Current" section were updated (SAR 24882 and SAR 24112).	2-7
	VJTAG was removed from Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Sleep Mode* (SARs 24112, 24882, and 79503).	2-8
	The note stating what was included in I_{DD} was removed from Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Shutdown Mode. The note, "per VCCI or VJTAG bank" was removed from Table 2-12 • Quiescent Supply Current (IDD), No IGLOO nano Flash*Freeze Mode[1]. The note giving I_{DD} was changed to "I_{DD} = N_{BANKS} * I_{CCI} + I_{CCA}."	2-8
	The values in Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings and Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1] were updated. Wide range support information was added.	2-9

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "IGLOO nano Device Status" table on page III, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Unmarked (production)

This version contains information that is considered to be final.

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